

## CLAIMS

1. A compound semiconductor substrate for epitaxial growth, wherein  
when haze is defined as a value calculated by dividing intensity of scattered light obtained when light is incident from a predetermined light source onto a surface of a substrate, by intensity of the incident light from the light source,  
the haze is not more than 2 ppm all over an effectively used area of the substrate and an off-angle with respect to a plane direction is 0.05 to 0.10°.
2. The compound semiconductor substrate as claimed in claim 1, wherein  
the haze is not more than 1 ppm all over the effectively used area of the substrate.
3. The compound semiconductor substrate as claimed in claim 1 or 2, wherein  
the compound semiconductor substrate is an InP substrate.
4. The compound semiconductor substrate as claimed in claim 3, wherein  
a dislocation density is not more than 1000/cm<sup>2</sup>.

5. The compound semiconductor substrate as claimed in claim 4, wherein  
the dislocation density is not more than 500/cm<sup>2</sup>.